
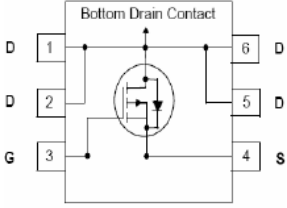




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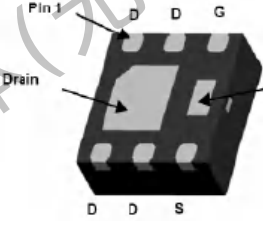
P-Channel Enhancement Mosfet

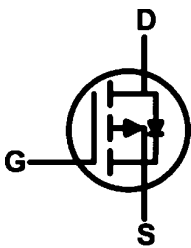
<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = -20V$ $I_D = -30A$</p> <p>$R_{DS(ON)} = 10m\Omega (typ.) @ V_{GS} = -4.5V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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Marking: 30P02 OR 20P02

BF6: PDFN2*2-6L





Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-30	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-11	A
I_{DM}	Pulsed Drain Current	-68	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	18	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	4.2	$^\circ C/W$

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Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.012	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-10A	---	10	15	mΩ
		V _{GS} =-2.5V, I _D =-8A	---	13	18	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.65	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2.94	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-15V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	---	43	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-10A	---	35	---	nC
Q _{gs}	Gate-Source Charge		---	5.0	---	
Q _{gd}	Gate-Drain Charge		---	10	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-10A	---	12.0	---	ns
T _r	Rise Time		---	40.0	---	
T _{d(off)}	Turn-Off Delay Time		---	30	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	2800	---	pF
C _{oss}	Output Capacitance		---	690	---	
C _{rss}	Reverse Transfer Capacitance		---	590	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-30	A
I _{SM}	Pulsed Source Current		---	---	---	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-10A, dI/dt=100A/μs, T _J =25°C	---	27	---	nS
Q _{rr}	Reverse Recovery Charge		---	17.8	---	nC

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Typical Characteristics

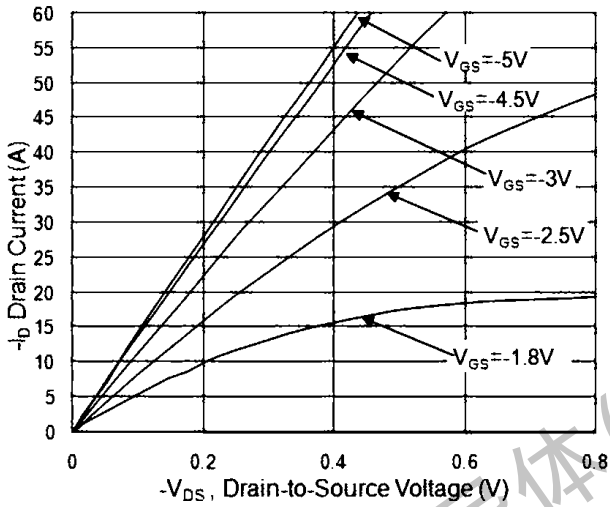


Fig.1 Typical Output Characteristics

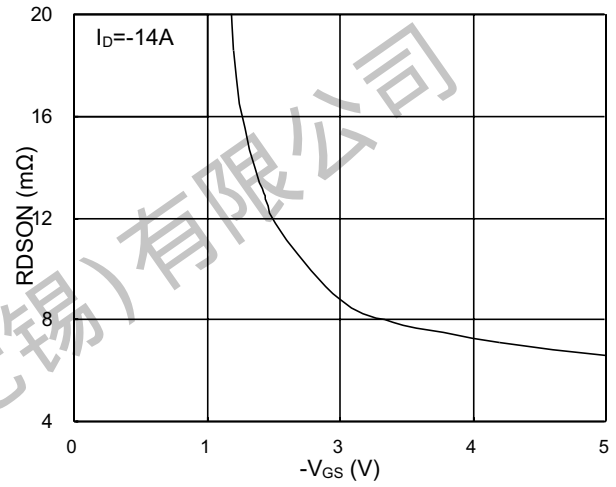


Fig.2 On-Resistance vs. G-S Voltage

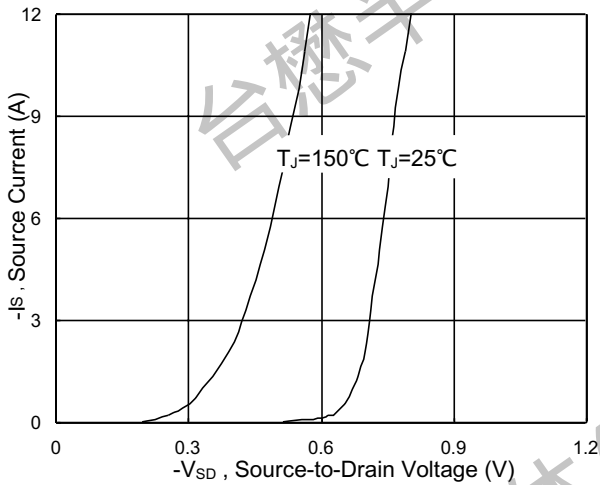


Fig.3 Forward Characteristics of Reverse

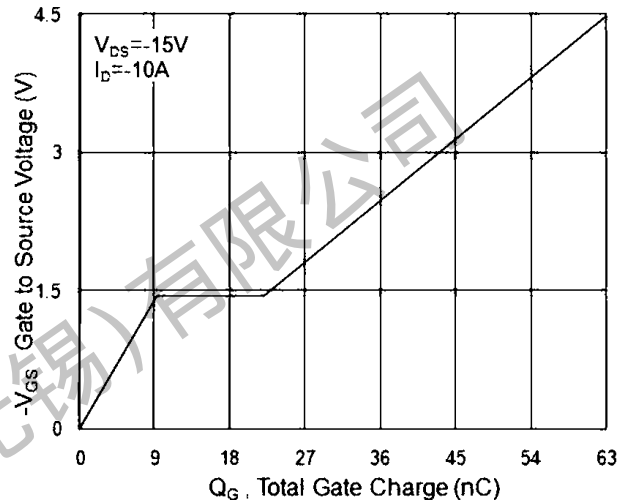


Fig.4 Gate-charge Characteristics

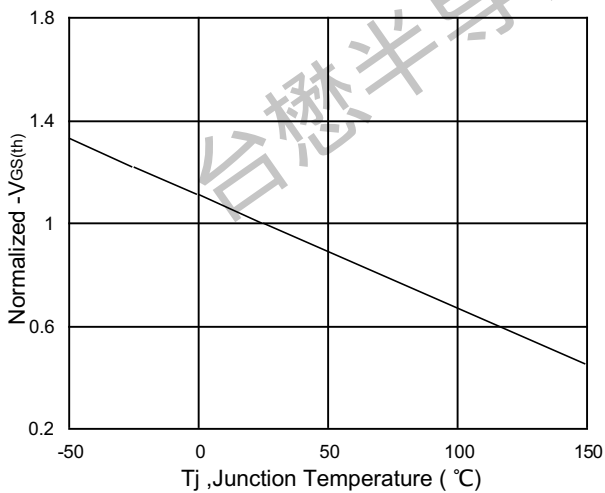


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

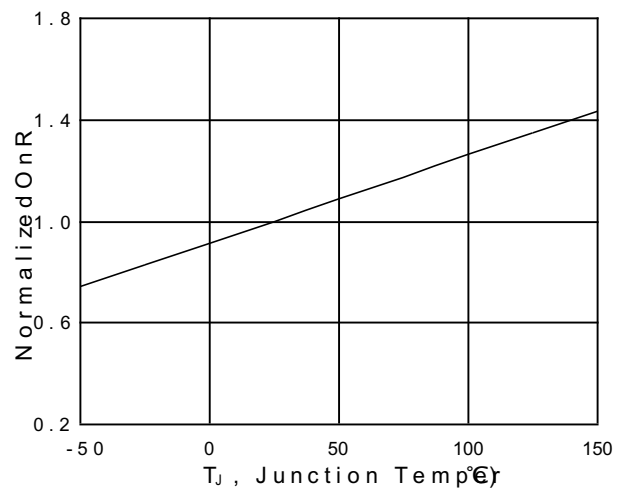


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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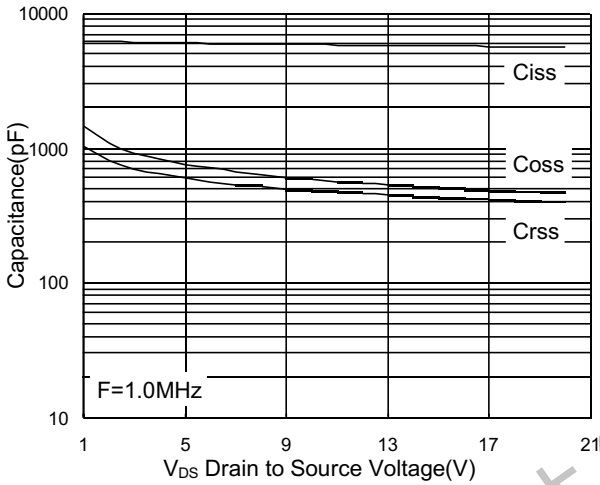


Fig.7 Capacitance

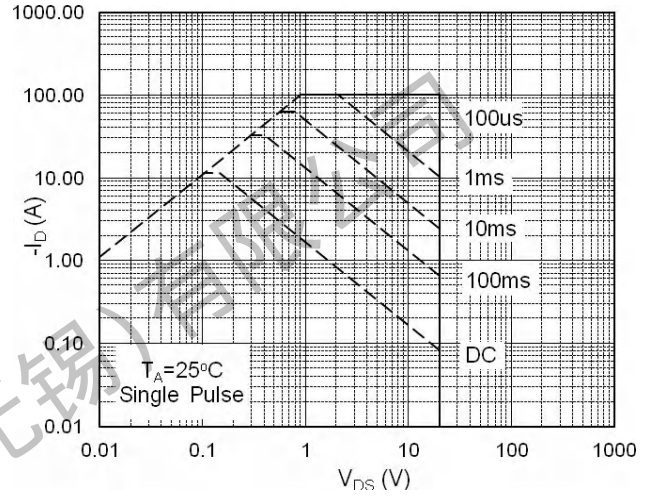


Fig.8 Safe Operating Area

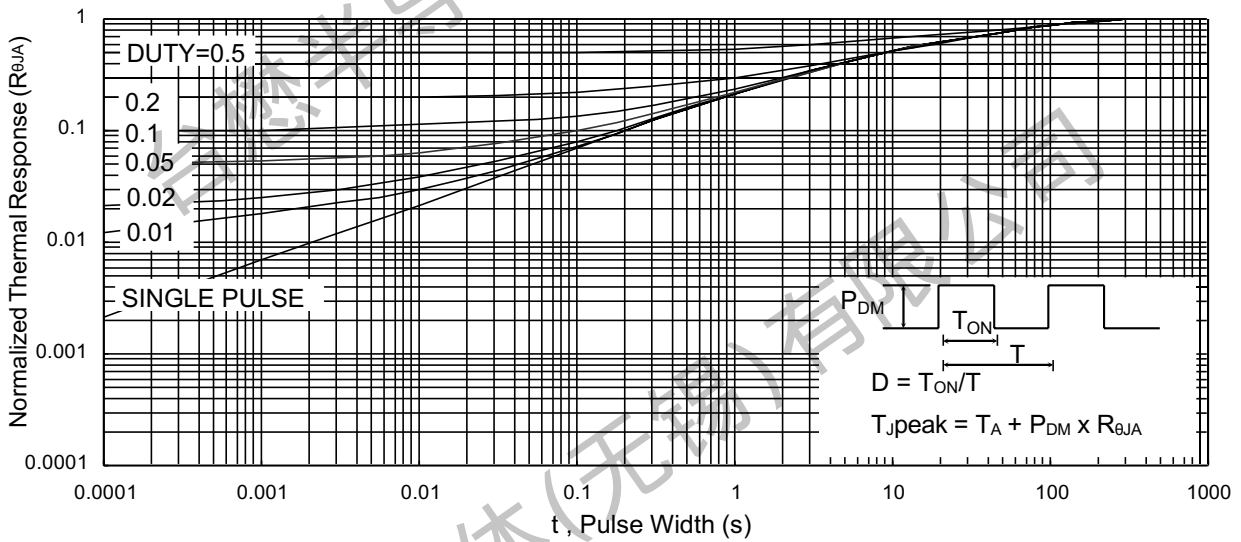


Fig.9 Normalized Maximum Transient Thermal Impedance

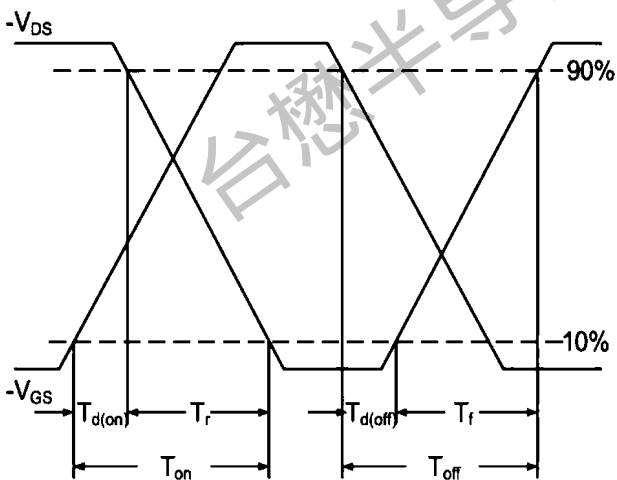


Fig.10 Switching Time Waveform

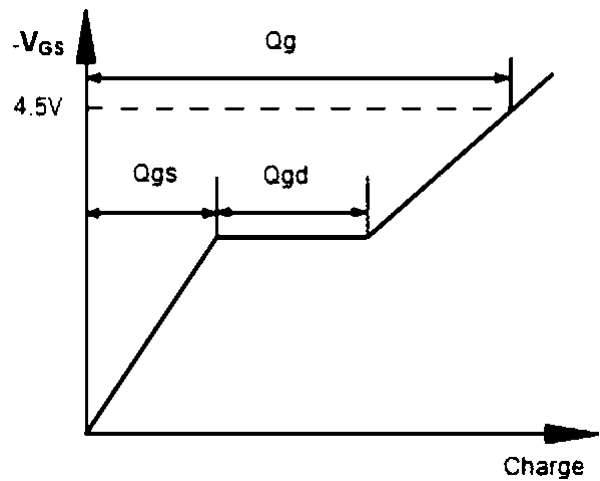
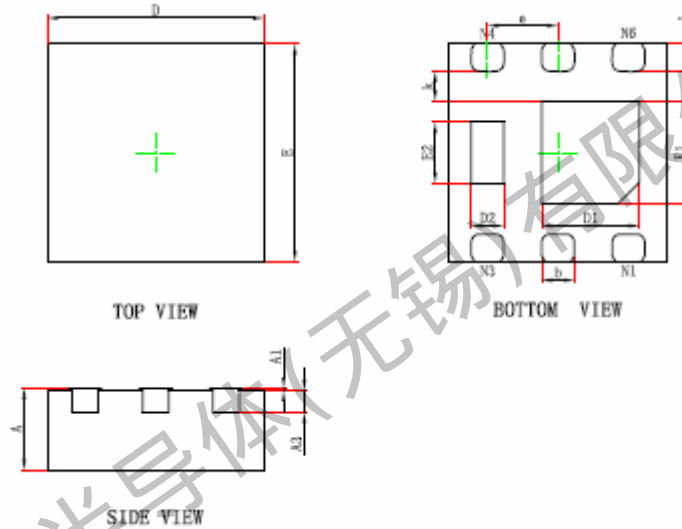


Fig.11 Gate Charge Waveform

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Package Mechanical Data: PDFN2*2-6L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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Revision history:

Date	Rev	Description	Page
2023.07.21	23.07	Original	